



South Sea Semiconductor

SSS8205

Dual N-Channel Enhancement Mode MOSFET

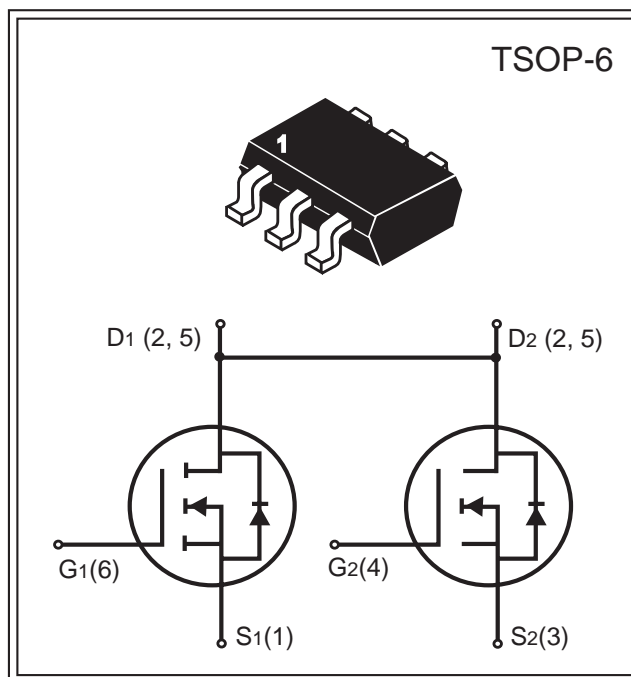
Product Summary

V _{DS} (V)	I _D (A)	R _{DS(ON)} (mΩ) Max
20V	4A	30 @V _{GS} = 4.5V
		45 @V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount package.

TSOP-6



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±10	V
Drain Current-Continuous @ T _J = 25°C	I _D	4	A
-Pulsed ^b	I _{DM}	25	A
Drain-Source Diode Forward Current ^a	I _S	2	A
Maximum Power Dissipation ^a	P _D	1.25	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R _{JA}	100	°C/W
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South Sea Semiconductor reserves the right to make changes to improve reliability or manufacturability without advance notice.

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Electrical Characteristics (T _A = 25°C unless otherwise noted)						
Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250 μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	μA
Gate-Body Leakage	I _{GSS}	V _{GS} = ± 8V, V _{DS} =0V			± 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =250 μA	0.6	0.8	1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4A		28	30	m
		V _{GS} =2.5V, I _D =3A		35	45	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =4A		12		S
Input Capacitance	C _{ISS}	V _{DS} =8V		802		pF
Output Capacitance	C _{OSS}	V _{GS} =0V		153		
Reverse Transfer Capacitance	C _{RSS}	f=1.0MHz		122		
Turn-On Delay Time	t _{D(ON)}	V _D =10V, I _D =1A, V _{GEN} =4.5V, R _{GEN} =10 Ω, R _L =10 Ω		18		ns
Rise Time	t _r			5		
Turn-Off Delay Time	t _{D(OFF)}			43.8		
Fall Time	t _f			20		
Total Gate Charge	Q _g	V _{DS} =10V, I _D =4A, V _{GS} =4.5V		10.5		nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			2.5		
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _D =2A		0.82	1.2	V

Notes :

- Surface Mounted on FR4 Board, t ≤ 10 sec.
- Pulse Test : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

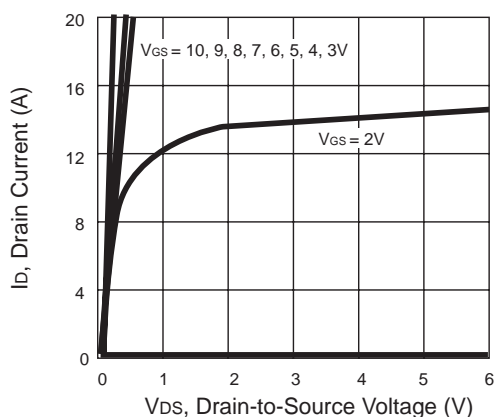


Figure 1. Output Characteristics

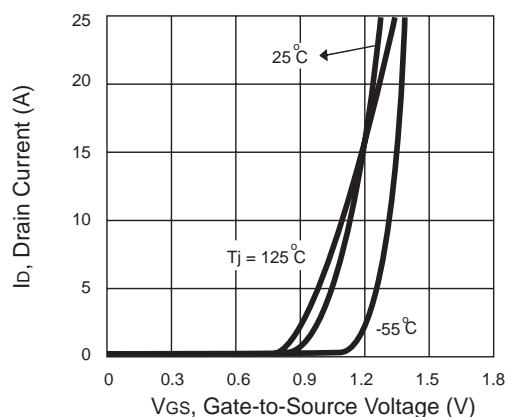


Figure 2. Transfer Characteristics

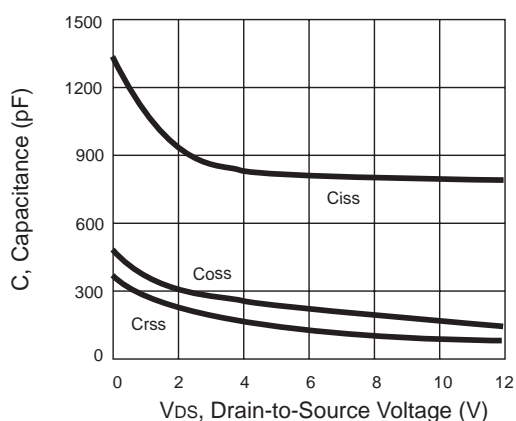


Figure 3. Capacitance

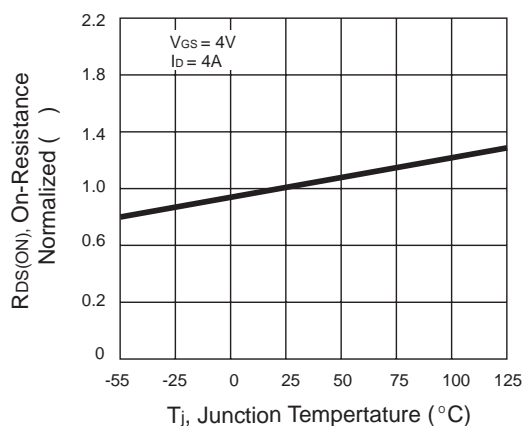


Figure 4. On-Resistance Variation with Temperature

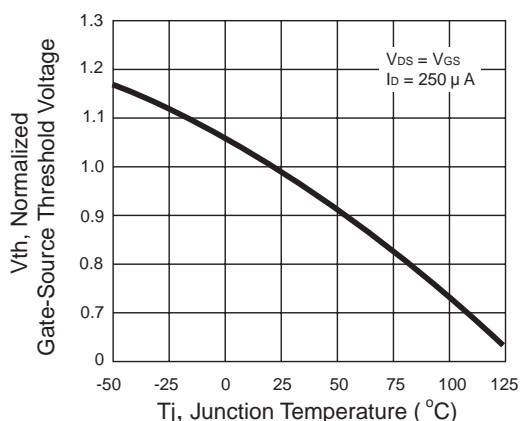


Figure 5. Gate Threshold Variation with Temperature

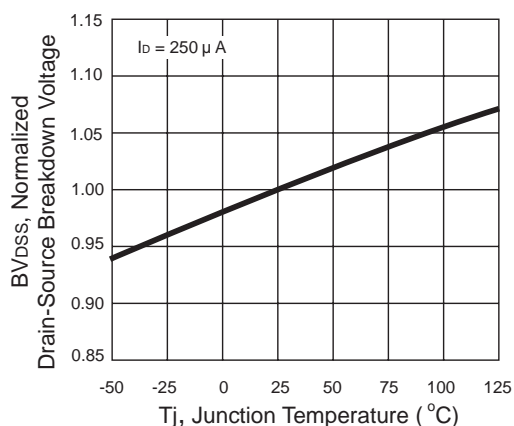


Figure 6. Breakdown Voltage Variation with Temperature

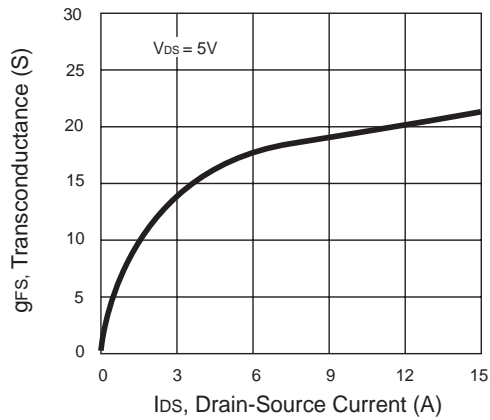


Figure 7. Transconductance Variation with Drain Current

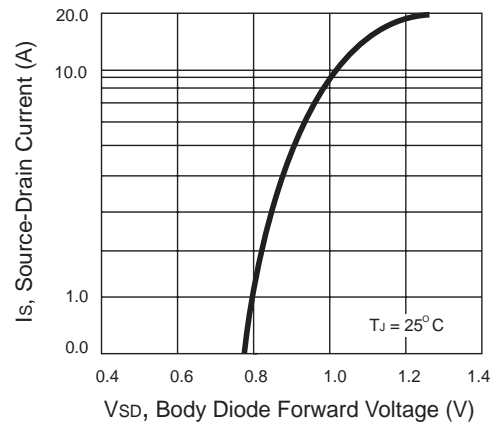


Figure 8. Body Diode Forward Voltage Variation with Source Current

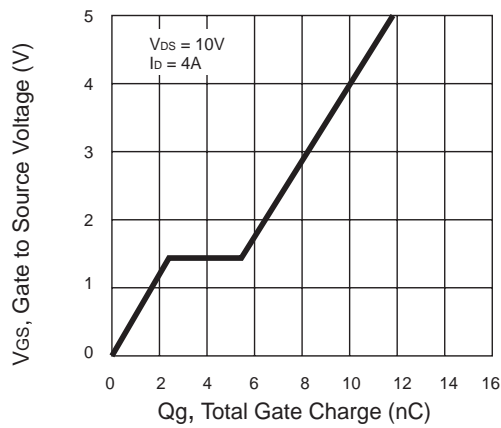


Figure 9. Gate Charge

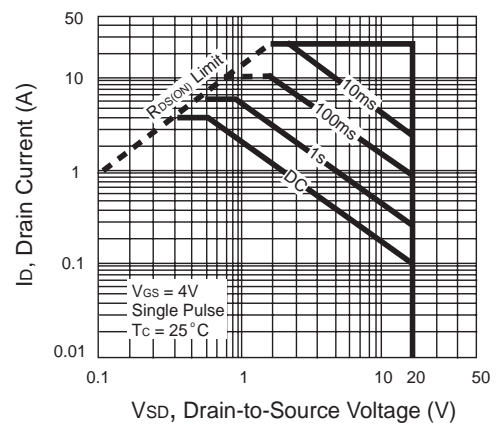


Figure 10. Maximum Safe Operating Area

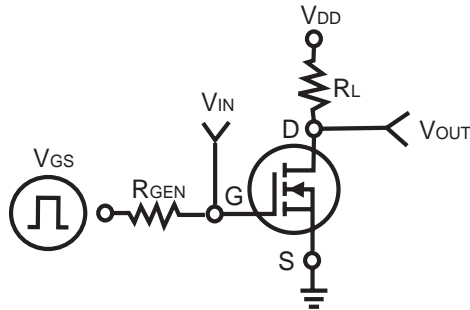


Figure 11. Switching Test Circuit

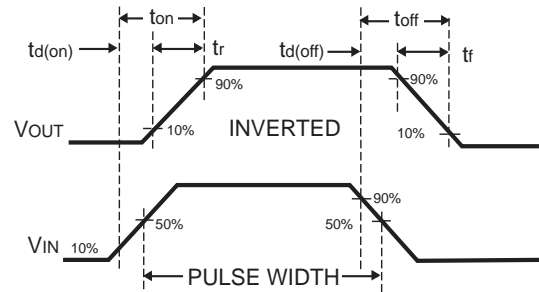


Figure 12. Switching Waveforms

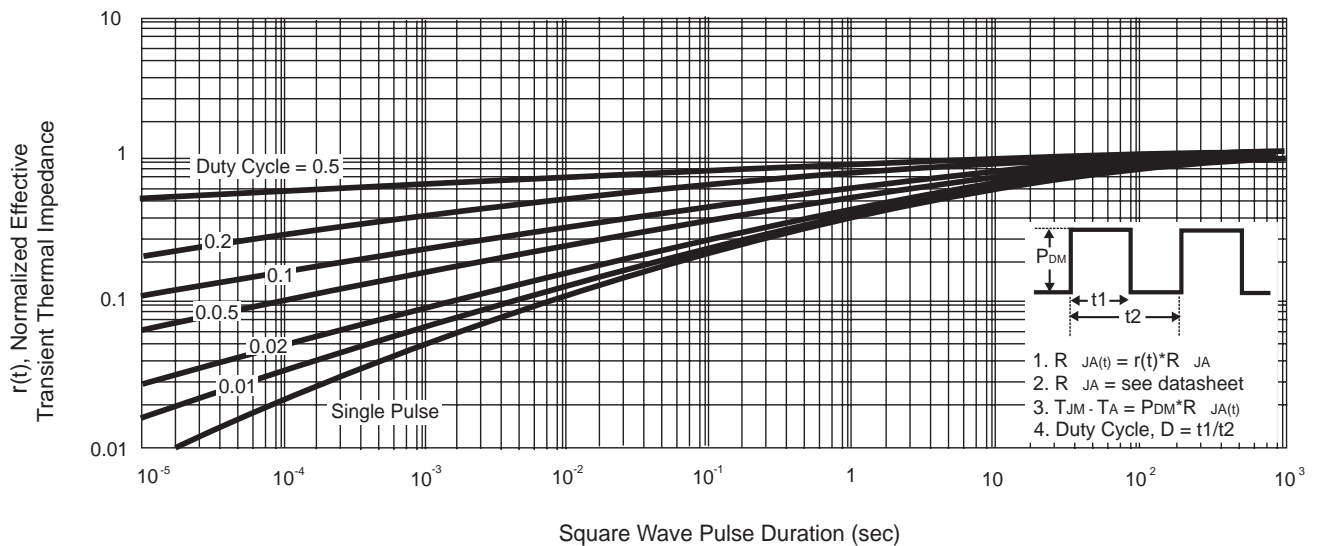
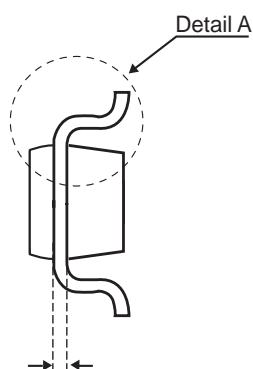
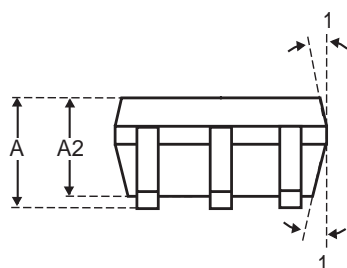
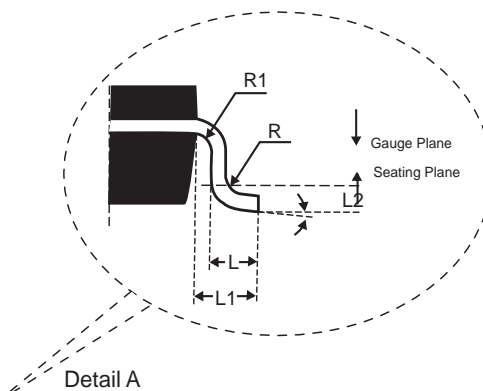
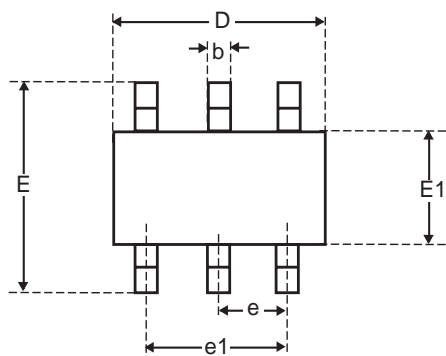


Figure 13. Normalized Thermal Transient Impedance Curve



Package Outline Dimensions

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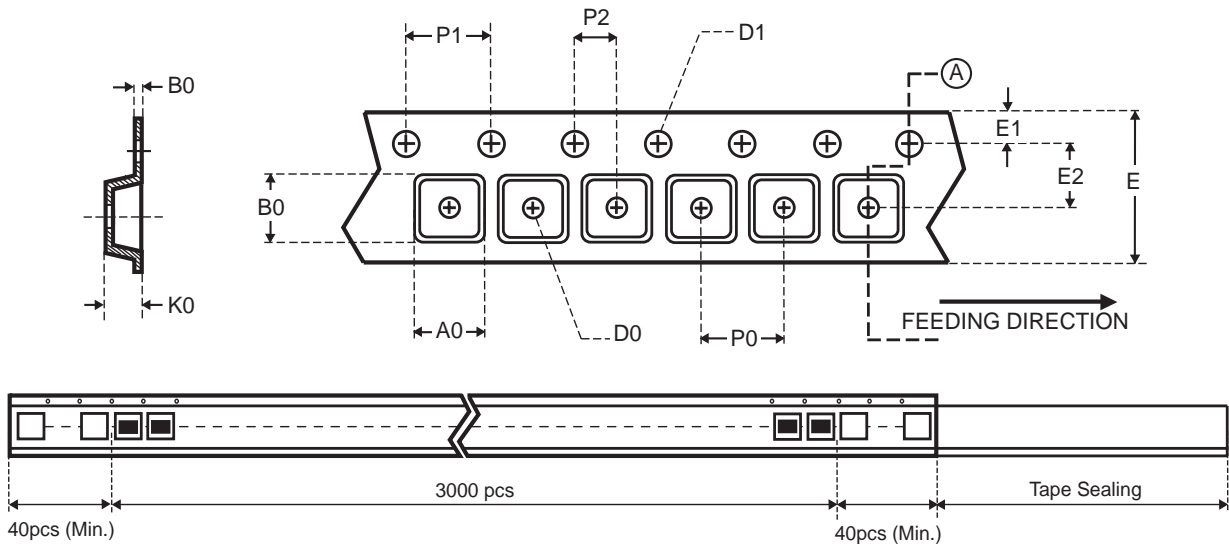


SYMBOLS	MILLIMETERS		
	Min.	Nom.	Max.
A	-	-	1.45
A2	0.90	0.15	1.30
b	0.30	-	0.50
c	0.08	-	0.22
D	2.70	2.90	3.10
E	2.50	2.80	3.10
E1	1.50	1.60	1.70
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.45	0.60
L1	0.60 BSC		
L2	0.20 BSC		
R	0.10	-	-
R1	0.10	-	0.25
	0°	4°	8°
1	0°	10°	15°



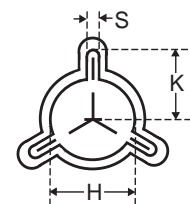
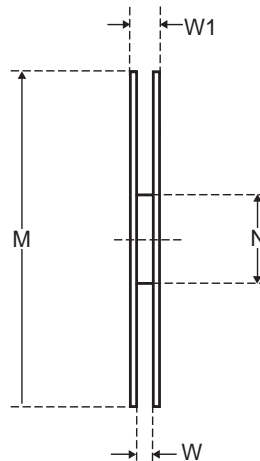
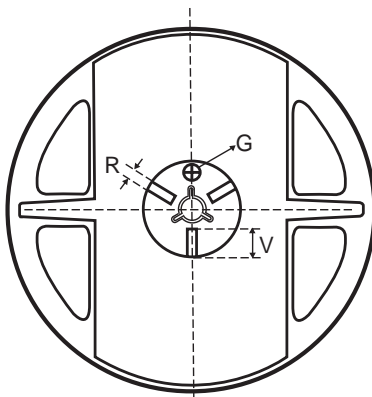
Carrier Tape & Reel Dimensions

TSOP-6



	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	
TSOP-6	3.15	3.20	1.40	1.50 +0.10 -0.00	1.50 +0.10 -0.00	8.00 ±0.30	1.75	3.50 ±0.05	4.00	4.00	2.00 ±0.05	0.20 ±0.03

UNIT : mm



Tape size	Reel Size	M	N	W	W1	H	K	S	G	R	V
8mm	178	178 ± 1	60 ± 1	8.4 ± 0.5	11.4 -0.5	13.5 ± 0.5	10.5	2.0 ± 0.5	10.0	5.0	18.0

UNIT : mm